

# SANYO Semiconductors

# DATA SHEET



### N-Channel Silicon MOSFET **CPH6445** — General-Purpose Switching Device **Applications**

### **Features**

- Low ON-resistance.
- 4V drive.

### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		60	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		3.5	А
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10µs, duty cycle≤1%	14	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm <sup>2</sup> x0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	60			V
Zero-Gate Voltage Drain Current	IDSS	VDS=60V, VGS=0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =1.5A	1.2	2.0		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=1.5A, VGS=10V		92	117	mΩ
	R <sub>DS</sub> (on)2	ID=0.7A, VGS=4.5V		120	168	mΩ
	R <sub>DS</sub> (on)3	ID=0.7A, VGS=4V		132	185	mΩ

Marking : ZX

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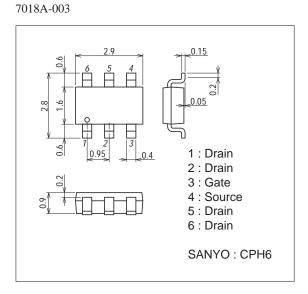
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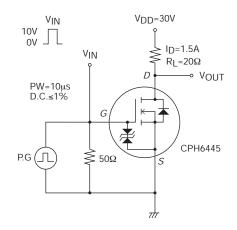
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz		310		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		40		pF
Reverse Transfer Capacitance	Crss	VDS=20V, f=1MHz		25		рF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		6.0		ns
Rise Time	tr	See specified Test Circuit.		5.5		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		27		ns
Fall Time	tf	See specified Test Circuit.		13		ns
Total Gate Charge	Qg	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =3.5A		6.8		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =3.5A		1.1		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =3.5A		1.4		nC
Diode Forward Voltage	V <sub>SD</sub>	IS=3.5A, VGS=0V		0.85	1.2	V

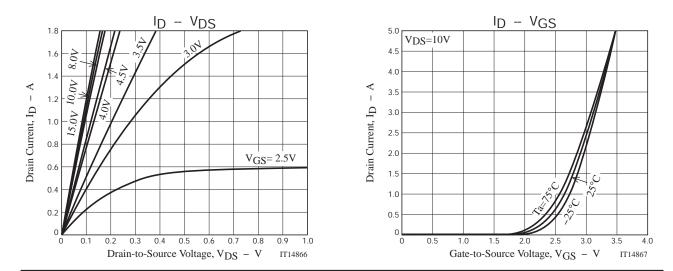
#### Package Dimensions

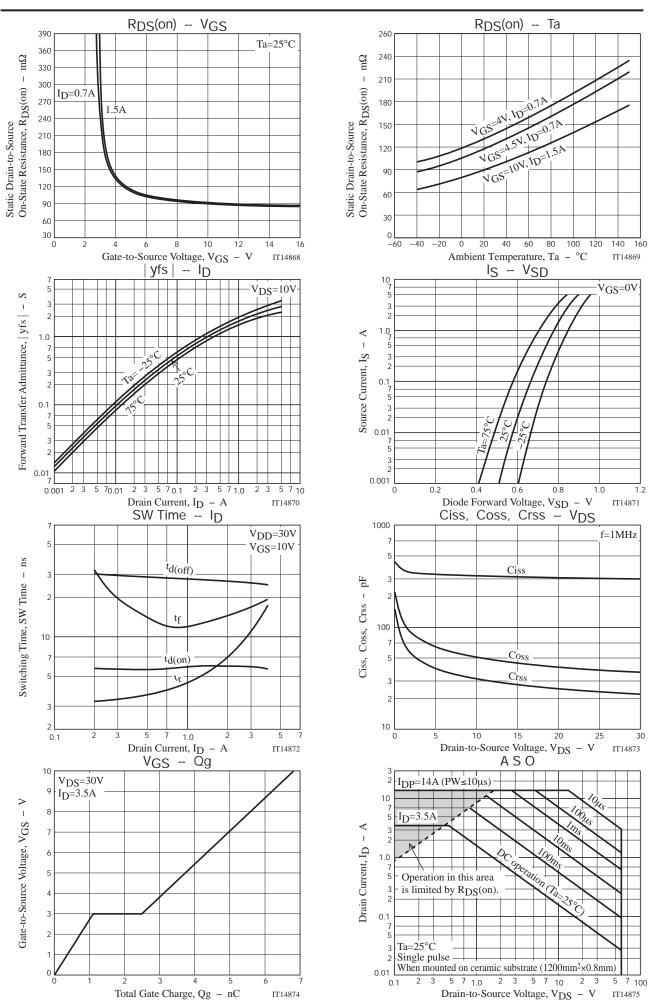
unit : mm (typ)

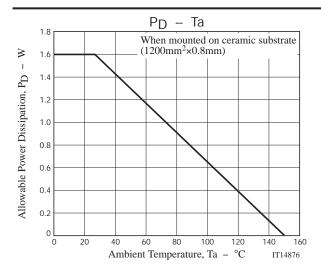


#### Switching Time Test Circuit









## Note on usage : Since the CPH6445 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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